

H5N2802PF

Silicon N Channel MOS FET
High Speed Power Switching

REJ03G1298-0100

Rev.1.00

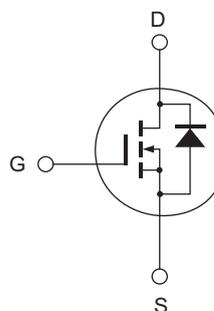
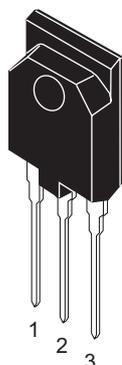
Oct.05.2005

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline

RENESAS Package code: PRSS0003ZA-A
(Package name: TO-3PFM)



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	280	V
Gate to source voltage	V_{GSS}	± 30	V
Drain current	I_D	25	A
Drain peak current	$I_{D(pulse)}^{Note1}$	100	A
Body-drain diode reverse drain current	I_{DR}	25	A
Body-drain diode reverse drain peak current	$I_{DR(pulse)}^{Note1}$	100	A
Avalanche current	I_{AP}^{Note3}	13	A
Avalanche energy	E_{AR}^{Note3}	10.2	mJ
Channel dissipation	P_{ch}^{Note2}	60	W
Channel to case thermal impedance	θ_{ch-c}	2.08	°C/W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

2. Value at $T_c = 25^\circ C$

3. $STch = 25^\circ C$, $T_{ch} \leq 150^\circ C$

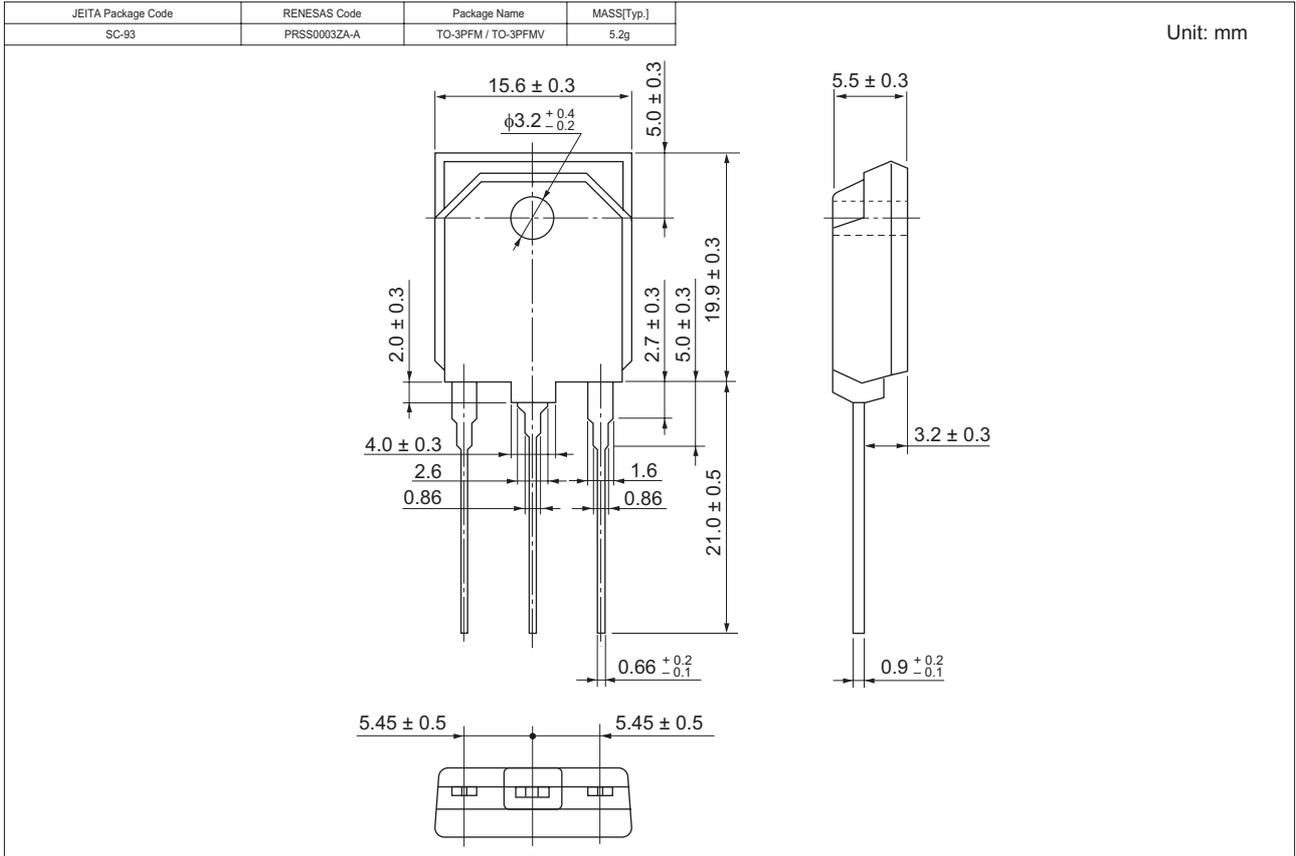
Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	280	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 280 \text{ V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 0.1	μA	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	—	4.0	V	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$
Forward transfer admittance	$ y_{fs} $	15	27	—	S	$I_D = 12.5 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note4}
Static drain to source on state resistance	$R_{DS(on)}$	—	0.057	0.066	Ω	$I_D = 12.5 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	3600	—	pF	$V_{DS} = 25 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	450	—	pF	
Reverse transfer capacitance	C_{rss}	—	32	—	pF	
Turn-on delay time	$t_{d(on)}$	—	50	—	ns	$I_D = 12.5 \text{ A}$, $V_{GS} = 10 \text{ V}$, $R_L = 11.2 \Omega$, $R_g = 10 \Omega$
Rise time	t_r	—	90	—	ns	
Turn-off delay time	$t_{d(off)}$	—	120	—	ns	
Fall time	t_f	—	75	—	ns	
Total gate charge	Q_g	—	72	—	nC	$V_{DD} = 220 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 25 \text{ A}$
Gate to source charge	Q_{gs}	—	18	—	nC	
Gate to drain charge	Q_{gd}	—	24	—	nC	
Body-drain diode forward voltage	V_{DF}	—	0.88	1.40	V	$I_F = 25 \text{ A}$, $V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	200	—	ns	$I_F = 25 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 100 \text{ A}/\mu\text{s}$
Body-drain diode reverse recovery charge	Q_{rr}	—	1.4	—	μC	

Notes: 4. Pulse test

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
H5N2802PF-E	30 pcs	Plastic magazine

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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